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National Semiconductor

October 2004

SCAN90CP02
1.5 Gbps 2x2 LVDS Crosspoint Switch with Pre-Emphasis and IEEE 1149.6

General Description

The SCAN90CP02 is a 1.5 Gbps 2 x 2 LVDS crosspoint switch. High speed data paths and flow-through pinout minimize internal device jitter, while configurable 0/25/50/100% pre-emphasis overcomes external ISI jitter effects of lossy backplanes and cables. The differential inputs interface to LVDS and Bus LVDS signals such as those on National's 10-, 16-, and 18- bit Bus LVDS SerDes, as well as CML and LVPECL. The SCAN90CP02 can also be used with ASICs and FPGAs. The non-blocking crosspoint architecture is pin-configurable as a 1:2 clock or data splitter, 2:1 redundancy mux, crossover function, or dual buffer for signal booster and stub hider applications.

Integrated IEEE 1149.1 (JTAG) and 1149.6 circuitry supports testability of both single-ended LVTTL/CMOS and differential LVDS PCB interconnect. The 3.3V supply, CMOS process, and LVDS I/O ensure high performance at low power over the entire industrial -40 to +85˚C temperature range.

Features

- 1.5 Gbps per channel
- Low power: 70 mA in dual repeater mode @1.5 Gbps
- Low output jitter
- Configurable 0/25/50/100% pre-emphasis drives lossy backplanes and cables
- Non-blocking architecture allows 1:2 splitter, 2:1 mux, crossover, and dual buffer configurations
- Flow-through pinout
- LVDS/BLVDS/CML/LVPECL inputs, LVDS Outputs
- IEEE 1149.1 and 1149.6 compliant
- Single 3.3V supply
- Separate control of inputs and outputs allows for power savings
- Industrial -40 to +85˚C temperature range
- 28-lead LLP package, or 32-lead LQFP package

Block Diagram

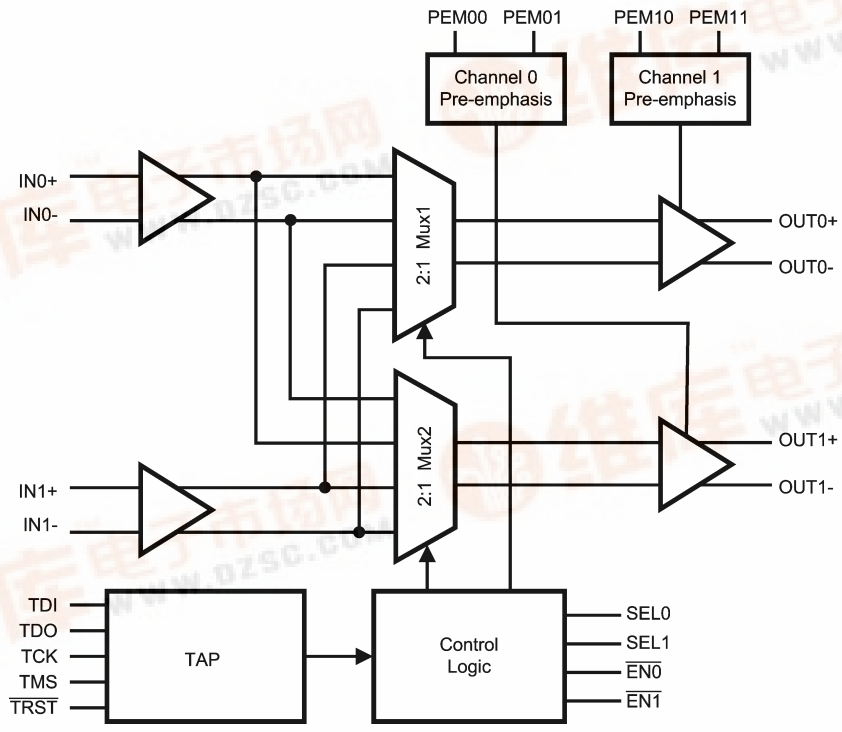

FIGURE 1. SCAN90CP02 Block Diagram

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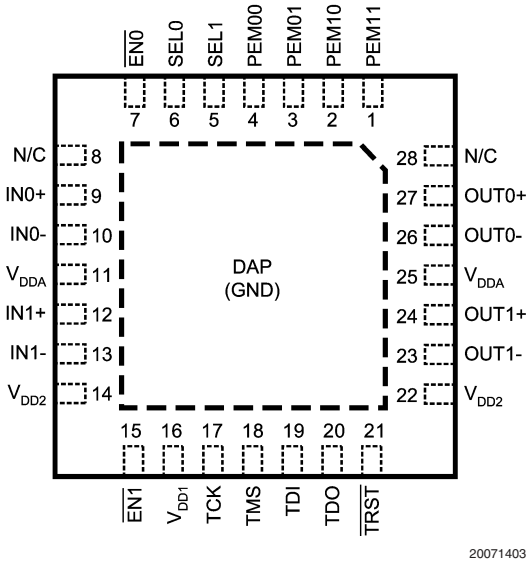
Pin Descriptions

Pin Name	LLP Pin Number	LQFP Pin Number	I/O, Type	Description
DIFFERENTIAL INPUTS COMMON TO ALL MUXES				
IN0+ IN0–	9 10	9 10	I, LVDS	Inverting and non-inverting differential inputs. LVDS, Bus LVDS, CML, or LVPECL compatible.
IN1+ IN1–	12 13	13 14	I, LVDS	Inverting and non-inverting differential inputs. LVDS, Bus LVDS, CML, or LVPECL compatible.
SWITCHED DIFFERENTIAL OUTPUTS				
OUT0+ OUT0–	27 26	32 31	O, LVDS	Inverting and non-inverting differential outputs. OUT0± can be connected to any one pair IN0±, or IN1±. LVDS compatible (Note 2).
OUT1+ OUT1–	24 23	28 27	O, LVDS	Inverting and non-inverting differential outputs. OUT1± can be connected to any one pair IN0±, or IN1±. LVDS compatible (Note 2).
DIGITAL CONTROL INTERFACE				
SEL0, SEL1	6 5	7 6	I, LVTTL	Select Control Inputs
$\overline{EN0}$, $\overline{EN1}$	7 15	8 17	I, LVTTL	Output Enable Inputs
PEM00, PEM01	4 3	4 3	I, LVTTL	Channel 0 Output Pre-emphasis Control Inputs
PEM10, PEM11	2 1	2 1	I, LVTTL	Channel 1 Output Pre-emphasis Control Inputs
TDI	19	22	I, LVTTL	Test Data Input to support IEEE 1149.1 features
TDO	20	23	O, LVTTL	Test Data Output to support IEEE 1149.1 features
TMS	18	21	I, LVTTL	Test Mode Select to support IEEE 1149.1 features
TCK	17	19	I, LVTTL	Test Clock to support IEEE 1149.1 features
$\overline{TRST}$	21	24	I, LVTTL	Test Reset to support IEEE 1149.1 features
N/C	8, 28			Not Connected
POWER				
V_{DD}	11, 14, 16, 22, 25	12, 16, 18, 25, 29	I, Power	V_{DD} = 3.3V ±0.3V. At least 4 low ESR 0.01 µF bypass capacitors should be connected from V_{DD} to GND plane.
GND	(Note 1)	5, 11, 15, 20, 26, 30		Ground reference to LVDS and CMOS circuitry. For the LLP package, the DAP is used as the primary GND connection to the device. The DAP is the exposed metal contact at the bottom of the LLP-28 package. It should be connected to the ground plane with at least 4 vias for optimal AC and thermal performance.

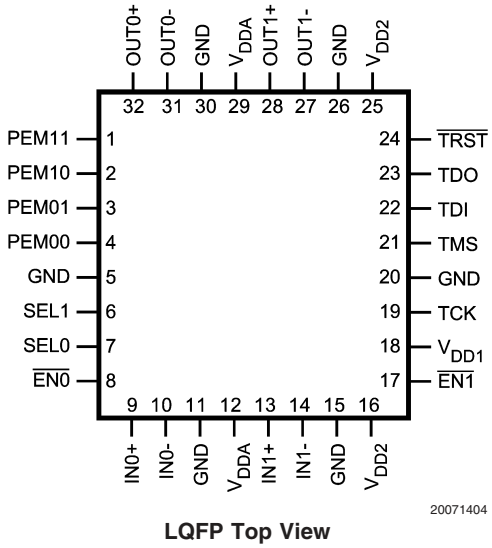
Note 1: Note that for the LLP package GND is not an actual pin on the package, the GND is connected thru the DAP on the back side of the LLP package.

Note 2: The LVDS outputs do not support a multidrop (BLVDS) environment. The LVDS output characteristics of the SCAN90CP02 device have been optimized for point-to-point backplane and cable applications.

Connection Diagrams



LLP Top View
DAP = GND



LQFP Top View

Configuration Select Truth Table

SEL0	SEL1	$\overline{EN0}$	$\overline{EN1}$	OUT0	OUT1	Mode
0	0	0	0	IN0	IN0	1:2 Splitter (IN1 powered down)
0	1	0	0	IN0	IN1	Dual Channel Repeater
1	0	0	0	IN1	IN0	Dual Channel Switch
1	1	0	0	IN1	IN1	1:2 Splitter (IN0 powered down)
0	1	0	1	IN0	PD	Single Channel Repeater (Channel 1 powered down)
1	1	0	1	IN1	PD	Single Channel Switch (IN0 and OUT1 powered down)
0	0	1	0	PD	IN0	Single Channel Switch (IN1 and OUT0 powered down)
0	1	1	0	PD	IN1	Single Channel Repeater (Channel 0 powered down)
X	X	1	1	PD	PD	Both Channels in Power Down Mode
0	0	0	1			Invalid State*
1	0	0	1			Invalid State*
1	0	1	0			Invalid State*
1	1	1	0			Invalid State*

PD = Power Down mode to minimize power consumption
X = Don't Care
* Entering these states is not forbidden, however device operation is not defined in these states.

Pre-emphasis

The pre-emphasis is used to compensate for long or lossy transmission media. Separate pins are provided for each output to minimize power consumption. Pre-emphasis is programmable to be off or to preset values per the Pre-emphasis Control Selection Table.

Pre-emphasis Control Selection Table

Channel 0		Channel 1		Pre-emphasis
PEM01	PEM00	PEM11	PEM10	
0	0	0	0	0%
0	1	0	1	25%
1	0	1	0	50%
1	1	1	1	100%

Output Characteristics

The output characteristics of the SCAN90CP02 device have been optimized for point-to-point backplane and cable applications.

Applications Information

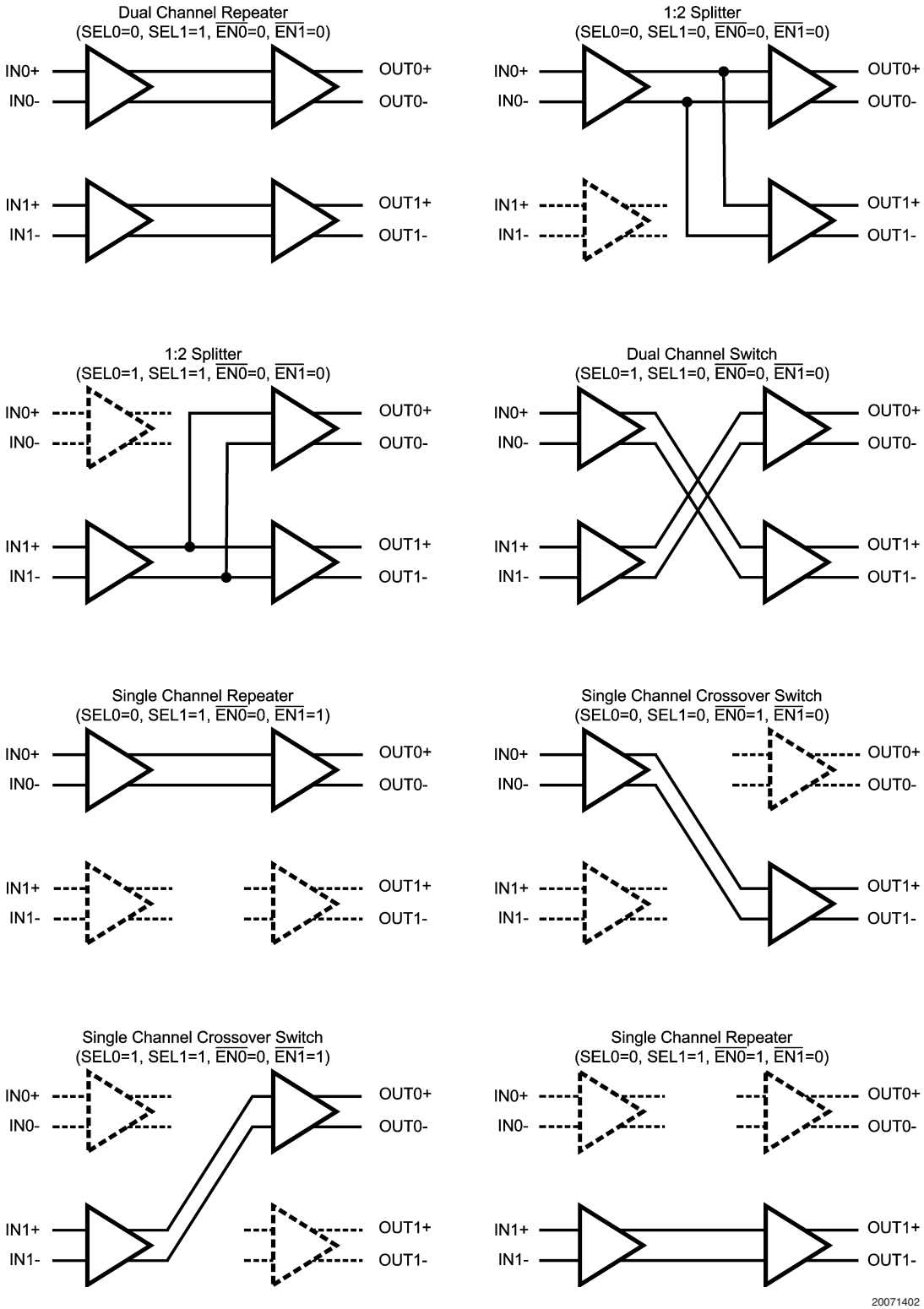


FIGURE 2. SCAN90CP02 Configuration Select Decode

Absolute Maximum Ratings (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V_{DD})	−0.3V to +4.0V
CMOS Input Voltage	−0.3V to (V_{DD} +0.3V)
LVDS Receiver Input Voltage	−0.3V to +3.6V
LVDS Driver Output Voltage	−0.3V to +3.6V
LVDS Output Short Circuit Current	40mA
Junction Temperature	+150˚C
Storage Temperature	−65˚C to +150˚C
Lead Temperature (Soldering, 4sec.)	+260˚C
Maximum Package Power Dissipation at 25˚C	
LLP-28	4.31 W
LQFP-32	1.47W
Derating above 25˚C	
LLP-28	34.5 mW/˚C
LQFP-32	11.8 mW/˚C
Thermal Resistance, θ_{JA}	
LLP-28	29˚C/W
LQFP-32	85˚C/W
ESD Rating	
HBM, 1.5 kΩ, 100 pF	6.5 kV
EIAJ, 0Ω, 200 pF	>250V

Recommended Operating Conditions

	Min	Typ	Max	Unit
Supply Voltage (V_{DD}− GND)	3.0	3.3	3.6	V
Receiver Input Voltage	0		3.6	V
Operating Free Air Temperature	−40	25	85	˚C
Junction Temperature			150	˚C

Electrical Characteristics

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	Typ (Note 4)	Max	Units
LVTTL DC SPECIFICATIONS (SEL0, SEL1, $\overline{EN1}$, $\overline{EN2}$, PEM00, PEM01, PEM10, PEM11, TDI, TCK, TMS, $\overline{TRST}$)						
V_{IH}	High Level Input Voltage		2.0		V_{DD}	V
V_{IL}	Low Level Input Voltage		GND		0.8	V
I_{IH}	High Level Input Current	$V_{IN} = V_{DD} = V_{DDMAX}$	−10		+10	µA
I_{IL}	Low Level Input Current	$V_{IN} = V_{SS}$, $V_{DD} = V_{DDMAX}$	−10		+10	µA
I_{ILR}	Low Level Input Current	TDI, TMS, $\overline{TRST}$	-40		-200	µA
C_{IN1}	Input Capacitance	Any Digital Input Pin to V_{SS}		3.5		pF
C_{OUT1}	Output Capacitance	Any Digital Output Pin to V_{SS}		5.5		pF
V_{CL}	Input Clamp Voltage	I_{CL} = −18 mA	−1.5	−0.8		V
V_{OH}	High Level Output Voltage (TDO)	I_{OH} = −12 mA, V_{DD} = 3.0 V	2.4			V
		I_{OH} = −100 µA, V_{DD} = 3.0 V	V_{DD}-0.2			V
V_{OL}	Low Level Output Voltage (TDO)	I_{OL} = 12 mA, V_{DD} = 3.0 V			0.5	V
		I_{OL} = 100 µA, V_{DD} = 3.0 V			0.2	V
I_{OS}	Output Short Circuit Current	TDO	-15		-125	mA
LVDS INPUT DC SPECIFICATIONS (IN0±, IN1±)						
V_{TH}	Differential Input High Threshold (Note 5)	V_{CM} = 0.8V or 1.2V or 3.55V, V_{DD} = 3.6V		0	50	mV
V_{TL}	Differential Input Low Threshold	V_{CM} = 0.8V or 1.2V or 3.55V, V_{DD} = 3.6V	−50	0		mV
V_{ID}	Differential Input Voltage	V_{CM} = 0.8V to 3.55V, V_{DD} = 3.6V	100			mV
V_{CMR}	Common Mode Voltage Range	V_{ID} = 150 mV, V_{DD} = 3.6V	0.05		3.55	V
C_{IN2}	Input Capacitance	IN+ or IN− to V_{SS}		3.5		pF
I_{IN}	Input Current	V_{IN} = 3.6V, $V_{DD} = V_{DDMAX}$ or 0V	−10		+10	µA
		V_{IN} = 0V, $V_{DD} = V_{DDMAX}$ or 0V	−10		+10	µA

Electrical Characteristics (Continued)

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions		Min	Typ (Note 4)	Max	Units
LVDS OUTPUT DC SPECIFICATIONS (OUT0±, OUT1±)							
V_{OD}	Differential Output Voltage, 0% Pre-emphasis (Note 5)	R_L = 100Ω between OUT+ and OUT–		250	400	575	mV
ΔV_{OD}	Change in V_{OD} between Complementary States			–35		35	mV
V_{OS}	Offset Voltage (Note 6)			1.09	1.25	1.475	V
ΔV_{OS}	Change in V_{OS} between Complementary States			–35		35	mV
I_{OS}	Output Short Circuit Current, One Complementary Output	OUT+ or OUT– Short to GND			–15	-40	mA
		OUT+ or OUT– Short to V_{DD}			15	40	mA
I_{OSB}	Output Short Circuit Current, both Complementary Outputs	OUT+ and OUT– Short to GND			–15	-30	mA
		OUT+ and OUT– Short to V_{CM}			15	30	mA
C_{OUT2}	Output Capacitance	OUT+ or OUT– to GND when TRI-STATE			5.5		pF
SUPPLY CURRENT (Static)							
I_{CC0}	Supply Current	All inputs and outputs enabled and active, terminated with differential load of 100Ω between OUT+ and OUT-.			42	60	mA
I_{CC1}	Supply Current - one channel powered down	Single channel crossover switch or single channel repeater modes (1 channel active, one channel in power down mode)			22	30	mA
I_{CC2}	Supply Current - one input powered down	Splitter mode (One input powered down, both outputs active)			30	40	mA
I_{CCZ}	TRI-STATE Supply Current	Both input/output Channels in Power Down Mode			1.4	2.5	mA
SWITCHING CHARACTERISTICS—LVDS OUTPUTS (*Figures 3, 4*)							
t_{LHT}	Differential Low to High Transition Time	Use an alternating 1 and 0 pattern at 200 Mb/s, measure between 20% and 80% of V_{OD}.		70	150	215	ps
t_{HLT}	Differential High to Low Transition Time			50	135	180	ps
t_{PLHD}	Differential Low to High Propagation Delay	Use an alternating 1 and 0 pattern at 200 Mb/s, measure at 50% V_{OD} between input to output.		0.5	2.4	3.5	ns
t_{PHLD}	Differential High to Low Propagation Delay			0.5	2.4	3.5	ns
t_{SKD1}	Pulse Skew	$\lvert t_{PLHD} - t_{PHLD} \rvert$			55	120	ps
t_{SKCC}	Output Channel to Channel Skew	Difference in propagation delay (t_{PLHD} or t_{PHLD}) among all output channels in Splitter mode (any one input to all outputs).		0	130	315	ps
t_{JIT} t_{ON}	Jitter (0% Pre-emphasis) (Note 7)	RJ - Alternating 1 and 0 at 750 MHz			1.4	2.5	psrms
		DJ - K28.5 Pattern 1.5 Gbps	LQFP		110	140	psp-p
			LLP		42	75	psp-p
		TJ - PRBS 2^{23}-1 Pattern 1.5 Gbps	LQFP		125	160	psp-p
			LLP		105	140	psp-p
	LVDS Output Enable Time	Time from $\overline{ENx}$ to OUT± change from TRI-STATE to active.		50	110	150	ns
t_{OFF}	LVDS Output Disable Time	Time from $\overline{ENx}$ to OUT± change from active to TRI-STATE.			5	12	ns

Electrical Characteristics (Continued)

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	Typ (Note 4)	Max	Units
t_{SW}	LVDS Switching Time SELx to OUT±	Time from configuration select (SELx) to new switch configuration effective for OUT±.		110	150	ns

SCAN Circuitry Timing Requirements

Symbol	Parameter	Conditions	Min	Typ	Max	Units
f_{MAX}	Maximum TCK Clock Frequency	R_L = 500Ω, C_L = 35 pF	25.0			MHz
t_S	TDI to TCK, H or L		1.0			ns
t_H	TDI to TCK, H or L		2.0			ns
t_S	TMS to TCK, H or L		2.0			ns
t_H	TMS to TCK, H or L		1.5			ns
t_W	TCK Pulse Width, H or L		10.0			ns
t_W	$\overline{TRST}$ Pulse Width, L		2.5			ns
t_{REC}	Recovery Time, $\overline{TRST}$ to TCK		2.0			ns

Note 3: "Absolute Maximum Ratings" are the ratings beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits.

Note 4: Typical parameters are measured at V_{DD} = 3.3V, T_A = 25˚C. They are for reference purposes, and are not production-tested.

Note 5: Differential output voltage V_{OD} is defined as ABS(OUT+−OUT−). Differential input voltage V_{ID} is defined as ABS(IN+−IN−).

Note 6: Output offset voltage V_{OS} is defined as the average of the LVDS single-ended output voltages at logic high and logic low states.

Note 7: JIT is the jitter from any input to any one differential LVDS output running at the specified data rate and data pattern, the other channel is powered off. Jitter is not production tested, but guaranteed through characterization on a sample basis. Random Jitter is measured RMS with a histogram including 1500 histogram window hits. K28.5 pattern is repeating bit streams of (0011111010 1100000101). This deterministic jitter or DJ pattern is measured to a histogram mean with a sample size of 350 hits. Total Jitter is measured peak to peak with a histogram including 3500 window hits.

Timing Diagrams

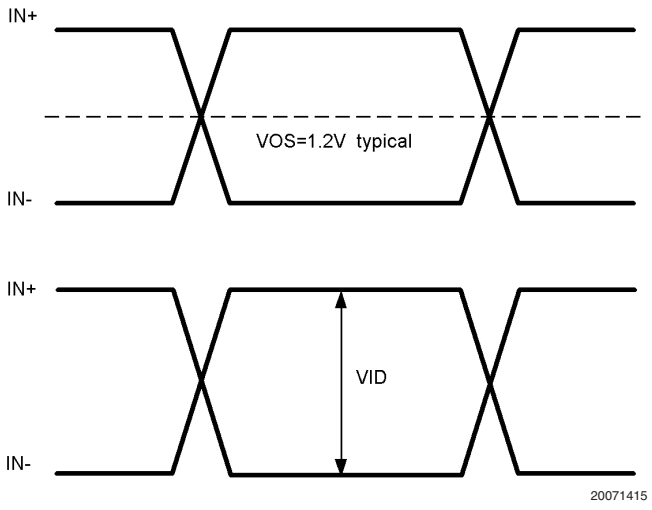


FIGURE 3. LVDS Signals

Timing Diagrams (Continued)

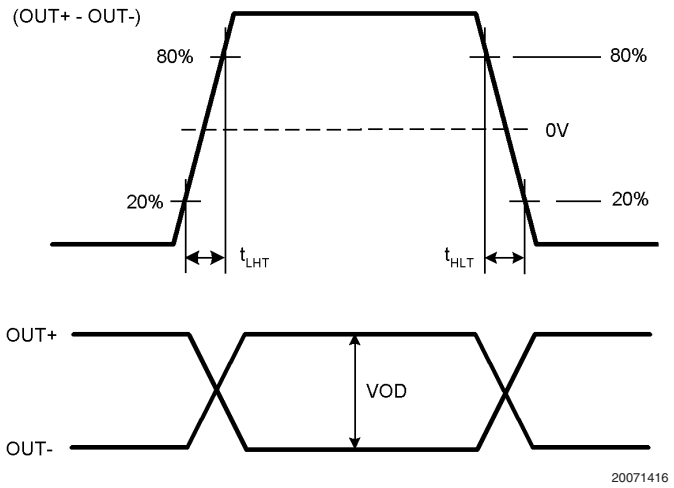


FIGURE 4. LVDS Output Transition Time

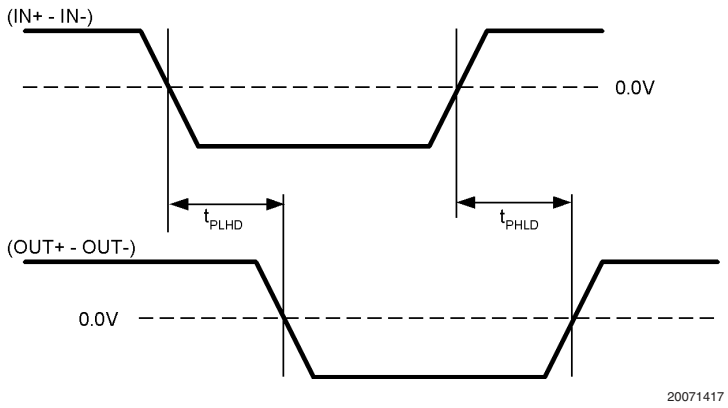


FIGURE 5. LVDS Output Propagation Delay

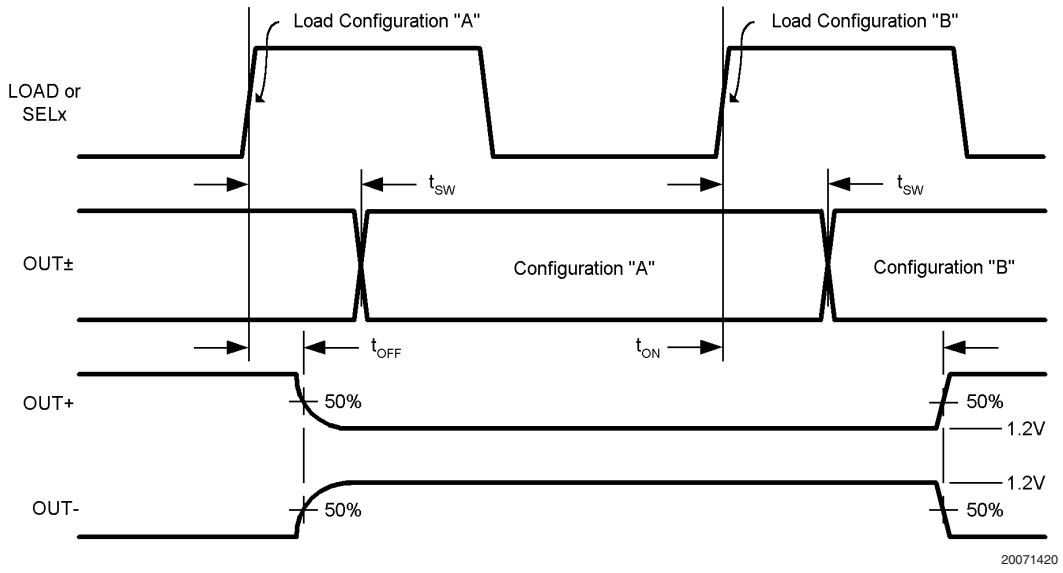
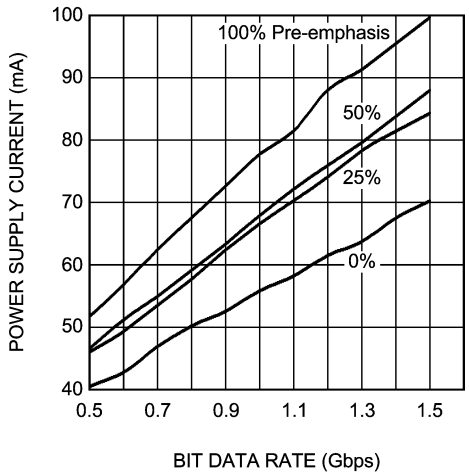


FIGURE 6. Configuration and Output Enable/Disable Timing

Typical Performance Characteristics for LLP Package

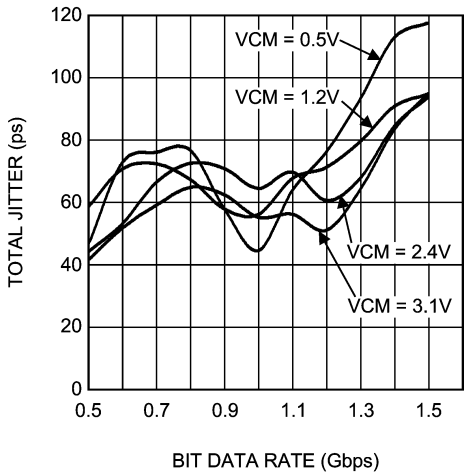
Power Supply Current vs. Bit Data Rate



20071441

Dynamic power supply current was measured while running a PRBS 2^{23}-1 pattern in dual channel repeater mode. V_{CC} = 3.3V, T_A = +25˚C, V_{ID} = 0.5V, V_{CM} = 1.2V

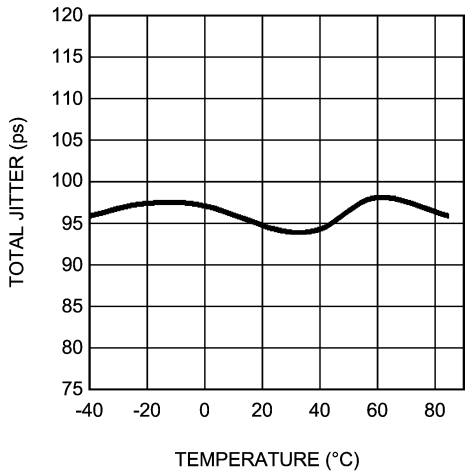
Total Jitter (T_J) vs. Bit Data Rate



20071442

Total Jitter measured at 0V differential while running a PRBS 2^{23}-1 pattern in single channel repeater mode. V_{CC} = 3.3V, T_A = +25˚C, V_{ID} = 0.5V, 0% Pre-emphasis

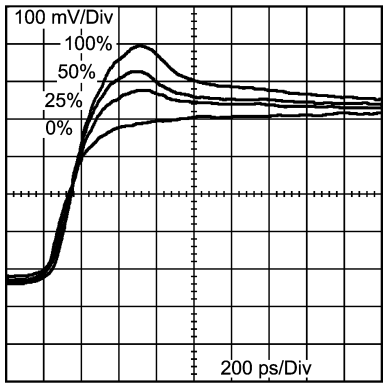
Total Jitter (T_J) vs. Temperature



20071443

Dynamic power supply current was measured while running a PRBS 2^{23}-1 pattern in dual channel repeater mode. V_{CC} = 3.3V, V_{ID} = 0.5V, V_{CM} = 1.2V, 1.5 Gbps data rate, 0% Pre-emphasis

Positive Edge Transition vs. Pre-emphasis Level



20071455

FIGURE 7. Typical Performance Characteristics

Design-For-Test (DfT) Features

IEEE 1149.1 SUPPORT

The SCAN90CP02 supports a fully compliant IEEE 1149.1 interface. The Test Access Port (TAP) provides access to boundary scan cells at each LVTTL I/O on the device for interconnect testing. The TAP also provides access to the IEEE 1149.6 test features if AC-coupled interconnects are used.

Refer to the BSDL file located on National's website for the details of the SCAN90CP02 IEEE 1149.1 implementation.

IEEE 1149.6 SUPPORT

AC-coupled differential interconnections on very high speed (1+ Gbps) data paths are not testable using traditional IEEE 1149.1 techniques. The IEEE 1149.1 structures and methods are intended to test static (DC-coupled), single ended networks. It is unable to test dynamic (AC-coupled) digital networks because the AC-coupling blocks static signals.

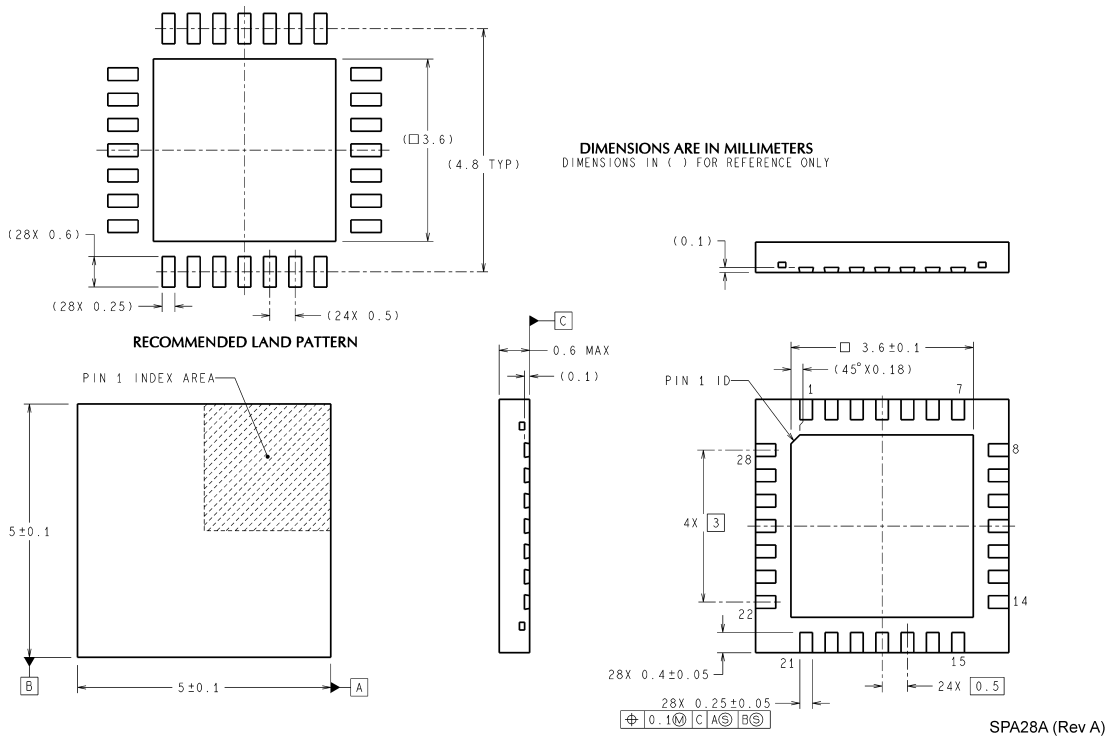
The SCAN90CP02 - which is intended for use in up to 1.5 Gbps data paths - has been designed with IEEE 1149.6 support to enable test of AC-coupled interconnects.

FAULT INSERTION

StuckAt is a feature that enables the user to override logic values on any of the external pins during normal operation. StuckAt can be thought of as having the same capabilities as the IEEE-1149.1 EXTEST instruction but on a per pin bases. Because this feature occurs on a per-pin basis, normal device operation (mission mode) is possible with the exception of the desired faults.

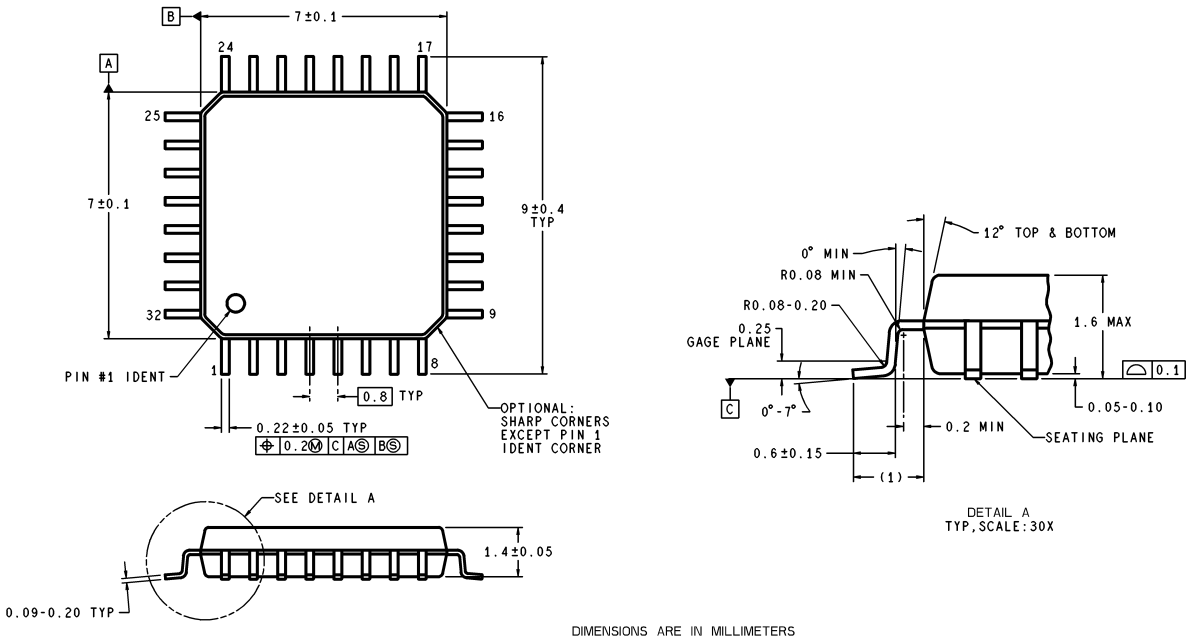
For more information on any of these features, refer to Application Note AN-1313, SCAN90CP02 Design-for-Test Features.

Physical Dimensions inches (millimeters) unless otherwise noted



LLP, Plastic, QUAD,
Order Number SCAN90CP02SP (1000 piece Tape and Reel),
SCAN90CP02SPX (4500 piece Tape and Reel)
NS Package Number SPA28A

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



DIMENSIONS ARE IN MILLIMETERS

VBE32A (Rev E)

LQFP, Plastic, Quad
Order Number SCAN90CP02VY (250 piece Tray)
SCAN90CP02VYX (1000 piece Tape and Reel)
NS Package Number VBE32A

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